

**SYNTHESIS OF MONOLAYER GRAPHENE ON POLYCRYSTALLINE NICKEL
AND NICKEL-COPPER BIMETALLIC CATALYST AND STUDY TOWARD THE
REUSE OF NICKEL CATALYST**

by

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TABLE OF CONTENTS

Acknowledgement.....	ii
Table of Content.....	iv
List of Tables	viii
List of Figures.....	ix
List of Abbreviations.....	xviii
List of Symbol.....	xxi
Abstrak	xxii
Abstract.....	xxiv

CHAPTER 1 - INTRODUCTION

1.1 Nanotechnology	1
1.2 Carbon element.....	3
1.3 Graphene.....	4
1.4 Methane.....	5
1.5 Problem statement.....	7
1.6 Objectives.....	9
1.7 Scope of study.....	9
1.8 Organization of the thesis.....	11

CHAPTER 2 - LITERATURE REVIEW

2.1 Introduction.....	13
2.2 Properties of graphene.....	14
2.3 Methods of graphene synthesis.....	15
2.3.1 Mechanical exfoliation.....	16

2.3.2	Wet chemical exfoliation.....	16
2.3.3	Sublimation of SiC.....	17
2.3.4	Chemical vapour deposition.....	19
2.3.4(a)	Hydrogen	21
2.3.4(b)	Temperature.....	22
2.3.4(c)	Carbon precursor.....	24
2.3.4(d)	Pressure.....	25
2.4	Catalysts.....	26
2.4.1	Ruthenium (Ru).....	27
2.4.2	Iridium (Ir).....	29
2.4.3	Platinum (Pt).....	30
2.4.4	Nickel (Ni).....	32
2.4.5	Copper (Cu).....	36
2.4.6	Nickel-Copper Bicatalyst (Ni-Cu)	43
2.5	Transfer of graphene.....	44
2.5.1	Mechanical exfoliation.....	44
2.5.2	Wet chemical etching.....	49
2.5.2(a)	Etchants.....	55
2.5.2(b)	Protective layers.....	57
2.6	Reuse of catalyst.....	61
2.7	Summary.....	63

CHPATER 3 - MATERIALS AND METHODS

3.1	Materials and Chemicals.....	64
3.2	Experimental equipment and rig set-up.....	66

3.2.1	Graphene growth rig.....	66
3.2.1(a)	Gas mixing section.....	66
3.2.1(b)	Reaction section.....	67
3.3	Experimental steps.....	74
3.3.1	Catalyst preparation.....	75
3.3.2	Production of graphene by CVD and process study.....	75
3.3.3	Controlled experiment for bilayer catalyst.....	77
3.3.4	Graphene separation.....	78
3.3.5	Study on the reuse and recycle of catalyst.....	79
3.4	Characterization.....	79
3.4.1	Raman spectroscopy.....	79
3.4.2	Atomic force microscopy.....	81
3.4.3	X-ray Diffraction	81
3.4.4	High Resolution Transmission Electron Microscopy (HRTEM), electron diffraction and Energy Dispersive Spectrometer (EDS).....	82
 CHAPTER 4 - RESULTS AND DISCUSSIONS		
4.1	Preliminary studies.....	84
4.1.1	Blank test on methane decomposition and preliminary studies of Ni and Cu foil for graphene formation.....	84
4.1.2	Preliminary test of graphene separation from Ni and Cu	87
4.2	Graphene formation on polycrystalline Cu foil.....	89
4.2.1	Temperature.....	89

4.2.2	Growth duration.....	91
4.2.3	Methane partial pressure.....	92
4.2.4	Summary.....	94
4.3	Graphene formation on polycrystalline Ni foil.....	94
4.3.1	Temperature.....	95
4.3.2	Growth duration.....	99
4.3.3	Methane partial pressure.....	105
4.3.4	Discussion	108
4.4	Graphene formation on a bilayer Ni-Cu catalyst.....	113
4.4.1	Temperature.....	115
4.4.2	Growth duration.....	119
4.4.3	Methane partial pressure.....	123
4.4.4	Discussion	125
4.5	Reuse and recycle of catalyst.....	130
4.5.1	Nitric acid.....	132
4.5.2	Iron nitrate solution.....	134
4.5.3	Discussion.....	138
 CHAPTER 5- CONCLUSION AND RECOMMENDATIONS		
5.1	Conclusions.....	149
5.2	Recommendations.....	151
	References.....	153

List of Publication

LIST OF TABLES

		Page
Table 1.1	Composition of raw natural gas (Gas Malaysia, 2011).	6
Table 2.1	General properties of transition metals mainly used to catalyse graphene growth.	45
Table 3.1	List of chemicals and reagents.	64
Table 3.2	Major component of the experiment rig and their function.	70
Table 3.3	Parameters list for CCVD study.	77
Table 3.4	Characteristic of different types of graphene in Raman spectra.	81
Table 4.1	Methane conversion recorded in the blank test.	86

LIST OF FIGURE

		Page
Figure 1.1	Diagram showing the nanotechnology region (Freie Universität Berlin, 2015)	2
Figure 1.2	Structures of selected allotropes of carbon. (Oganov <i>et al.</i> , 2013)	4
Figure 2.1	Graphene, the fundamental block of all dimensional carbon materials, such as fullerene (green), CNT (magenta) and graphite (cyan). (Geim and Novoselov, 2007)	14
Figure 2.2	Sketch of graphene formation steps on (a) Ni and (b) Cu (Losurdo <i>et al.</i> , 2011).	20
Figure 2.3	Summary of the interaction between graphene and transition metals. Yellow-labelled elements indicate weak interactions, and red and blue can be attributed to strong interactions and graphene grown from bulk carbide, respectively. “d” is the distance between graphene and metal (in scale of Angstrom), “c” indicates the buckling and corrugation of graphene (in scale of Angstrom), and “ π ” refers to the amount of downward shift of the Dirac point of graphene mounted on respective transition metals. ‘S’ or ‘M’ in the upper right corner of each element-box indicates if graphene forms single or multiple rotational domains (Batzill, 2012).	27
Figure 2.4	Graphene formation on (a) a single-crystal Ni(111) surface and (b) a polycrystalline Ni surface (Zhang <i>et al.</i> , 2010).	35
Figure 2.5	Illustration of the surface growth mechanism on Cu. Black particles indicate ^{13}C isotope, red particles indicate ^{12}C isotope and white particle indicates hydrogen (Li <i>et al.</i> , 2009b).	37

Figure 2.6	SEM images of graphene with (a) a hexagonal shape (Robertson and Warner, 2011), (b) a four-lobed flower shape (Li <i>et al.</i> , 2010), and (c) a dendrite shape (Fan <i>et al.</i> , 2011).	38
Figure 2.7	(a) Flow diagrams of the transfer process with heat treatment for (a) perforated substrate and (b) flat substrate (Suk <i>et al.</i> , 2011).	53
Figure 2.8	Schematic of the direct transfer of graphene onto a TEM grid (Regan <i>et al.</i> , 2010).	55
Figure 2.9	Schematic of the roll-based production of graphene films grown on a copper foil (Bae <i>et al.</i> , 2010).	61
Figure 2.10	Schematic of an electrolysis cell used for the electrochemical exfoliation of graphene from metal foil (Wang <i>et al.</i> , 2011c).	62
Figure 3.1	Photograph of the experimental rig set-up (Descriptions of parts according to numbers listed in Table 3.2).	68
Figure 3.2	Schematic diagram of the experimental rig set-up.	69
Figure 3.3	Flowchart of overall research activities of this study.	74
Figure 3.4	Cross-section view of the Cu-wrapped Ni catalyst that used for study.	75
Figure 3.5	Setup of the reaction zone of the reactor for the implication of fast cooling.	76
Figure 3.6	The built-up of the (a) Cu- SiO ₂ -Ni and (b) Cu-Ni- SiO ₂ catalysts used for the control experiment.	77
Figure 3.7	The steps for the sample preparation for obtaining EDS spectrum at the middle of Ni.	83
Figure 4.1	TEM images of the black powder collected on the wall of the	86

quartz tube that underwent CVD of 1150 °C. (a) Low magnification image and (b) High magnification image.

Figure 4.2	Raman spectra of graphitic materials grown on Ni and Cu with operating parameters of 950 °C, 10 min, 80 sccm of H ₂ and 80 sccm of CH ₄ .	87
Figure 4.3	Photographs of the graphene separation process by nitric acid with various concentrations (a) 21.67 %, (b) 6.7 % and (c) 3.35 %. The boxed area indicated the location of graphene.	88
Figure 4.4	Raman spectra of the graphitic materials grown on Cu foil with various temperatures. The growth duration was fixed at 5 min and 20 sccm of CH ₄ was diluted into 80 sccm of H ₂ .	90
Figure 4.5	Raman spectra of graphitic materials grown on Cu foil with various CVD durations at 950 °C and under 20 sccm of CH ₄ diluted into 80 sccm of H ₂ .	92
Figure 4.6	Raman spectra of graphitic materials grown on Cu foil with various partial pressure of CH ₄ . The growth duration was fixed at 5 min, and temperature was 950 °C.	93
Figure 4.7	Raman spectra of graphitic materials grown on Ni foil with various CVD temperatures at 5 min and under 20 sccm of CH ₄ diluted into 80 sccm H ₂ .	96
Figure 4.8	Raman maps showing I _{2D} /I _G for graphene grown on Ni at (a) 800 °C, (c) 850 °C and (e) 900 °C and fwhm _{2D} of graphene grown at (b) 800 °C, (d) 850 °C and (f) 900 °C. The growth duration was fixed at 5 min under the flow of 20 sccm of CH ₄ diluted into 80 sccm of H ₂ . Scale of maps 50µm x 50 µm.	97
Figure 4.9	HRTEM images of graphene grown on Ni at (a) 800 °C, (b) 850 °C and (c) 900 °C for 5 min under 20 sccm of CH ₄ diluted	98

into 80 sccm of H₂.

- Figure 4.10 Photograph of graphene sheet separated and deposited on a silicon wafer grown at 850 °C with 20 sccm of methane diluted into 80 sccm of hydrogen for (left) 4 min and (left) 5 min. 99
- Figure 4.11 Raman spectra of graphitic materials grown on Ni foil with various CVD durations at 850 °C under the flow of 20 sccm of CH₄ diluted into 80 sccm of H₂. 100
- Figure 4.12 Images from optical microscopy of graphene sheets separated and deposited onto a silicon wafer. Growth conditions: 850 °C, 20 sccm of methane diluted into 80 sccm of hydrogen for (a) 4 min and (b) 5 min. 101
- Figure 4.13 Raman maps of (a) I_{2D}/I_G and (b) fwhm_{2D} for graphene grown on Ni at 850 °C for 4 min under 20 sccm of CH₄ diluted into 80 sccm of H₂. 101
- Figure 4.14 HRTEM image of graphene grown on Ni foil at 850 °C for 4 min under 20 sccm of CH₄ and 80 sccm of H₂. 101
- Figure 4.15 Photograph of graphene sheets separated and deposited onto a silicon wafer. Growth conditions: 800 °C, 20 sccm of methane diluted into 80 sccm hydrogen for (left) 5 min (center), 6 min and (left) 7 min. 103
- Figure 4.16 Raman spectra of graphitic materials grown on Ni foil with various CVD durations at 800 °C under 20 sccm of CH₄ diluted into 80 sccm of H₂. 103
- Figure 4.17 Micrographs of the graphene sheets separated and deposited onto a silicon wafer. Growth conditions: 800 °C, 20 sccm of methane diluted into 80 sccm hydrogen for (a) 5 min (b) 6

min and (c) 7 min.

- Figure 4.18 Typical HRTEM image of graphene grown on Ni foil at 800 °C for 6 min under 20 sccm of CH₄ diluted into 80 sccm of H₂. 104
- Figure 4.19 Raman maps of I_{2D}/I_G for graphene grown on Ni at (a) 6 min and (c) 7 min of reaction and fwhm_{2D} map of graphene grown for (b) 6 min and (d) 7 min at 800 °C under of 20 sccm of CH₄ diluted into 80 sccm of H₂. 105
- Figure 4.20 Raman spectra of graphitic materials grown on Ni foil with various partial pressure of CH₄ at 850 °C and for 5 min. 106
- Figure 4.21 Photograph of graphene sheets separated and deposited onto a silicon wafer. Growth conditions: 850 °C for 5 min with various methane partial pressure of (left) 0.1 atm, (center) 0.2 atm and (right) 0.3 atm. 107
- Figure 4.22 Micrographs of the graphene sheets grown at 850 °C for 5 min and under methane partial pressure of (a) 0.1 atm, (b) 0.2 atm, (c) 0.3 atm and (d) 0.4 atm after separation and deposition onto silicon wafer. 107
- Figure 4.23 Phase diagram of nickel-carbon (left) and copper-carbon (right) bulk system. 108
- Figure 4.24 Cross-section view of the used bimetallic catalyst consisting of a Cu foil wrapping a Ni foil. 115
- Figure 4.25 Average and standard deviation of I_{2D}/I_G of graphene film obtained from graphene films grown on the 4 different surfaces of the CVD device in the temperature range 850 °C - 1000 °C for 5 min. 116

Figure 4.26	Micrographs of graphene grown at 950 °C for 5 min at the inner surfaces of (a) Ni and (b) Cu after transfer on silicon wafer.	117
Figure 4.27	Raman maps of I_{2D}/I_G for graphene grown on (a) Ni and (b) Cu, and $fwhm_{2D}$ for (c) Ni and (d) Cu at 950 °C for 5 min. The color gradient bar is given on the right of each map.	118
Figure 4.28	HRTEM images of monolayer graphene grown on inner surface of (a) Ni and (b) Cu at the edges, after CVD reaction at 950 °C for 5 min.	118
Figure 4.29	Average and standard deviation of I_{2D}/I_G of graphene film obtained from graphene film grown on the 4 different surfaces of the CVD device at 950 °C and for durations in the 4-8 min range.	119
Figure 4.30	Micrographs of the graphene materials transferred to silicon wafer after CVD growth for 4 min on (a) Ni and on (b) Cu; for 6 min on (c) Ni and (d) Cu; and for 7 min on (e) Ni and (f) Cu.	121
Figure 4.31	Raman maps of I_{2D}/I_G for graphene grown on (a) Ni and (b) Cu, and $fwhm_{2D}$ for (c) Ni and (d) Cu at 950 °C for 4 min. The color gradient bar is given on the right of each map.	122
Figure 4.32	HRTEM images of monolayer graphene grown on inner surface of (a) Ni and (b) Cu at the edges. Growth conditions: 950 °C and 4 min.	122
Figure 4.33	Average and standard deviation of I_{2D}/I_G of graphene films obtained at the 4 different surfaces of the CVD device at 950 °C for 5 min, the range of methane partial pressures being 0.2-0.6 atm.	123

Figure 4.34	Micrographs of graphene grown at the inner surface of (a) Ni and (b) Cu under methane partial pressure of 0.3 atm, respectively after transfer to silicon wafer (temperature growth 950 °C and duration 5 min).	123
Figure 4.35	Raman maps of I_{2D}/I_G for graphene grown on (a) Ni and (b) Cu, and $fwhm_{2D}$ for (c) Ni and (d) Cu at 950°C for 5 min, and methane partial pressure of 0.3. The color gradient bar is given on the right of each map.	124
Figure 4.36	HRTEM images of monolayer graphene grown on inner surface of (a) Ni and (b) Cu at the edges after CVD reaction at 950 °C for 5 min with a methane partial pressure of 0.3 atm.	124
Figure 4.37	TEM images of a Ni slice after the CVD reaction at 950 °C and 5 min with (a) low magnification image of the Ni strip; (b) Bright field TEM image in the area marked by the circle on the image (a); (c) Schematic showing the distribution on carbon adatoms at the middle of the Ni foil after the CVD reaction; grey areas indicating the grains of Ni and black dots illustrating the carbon adatoms.	127
Figure 4.38	EDS spectra of the cross-section area at the middle of the Ni foil as shown in Figure 4.37 at the middle of the grain in red at the grain boundary in black; magnified range from 0-1 keV is inserted at left top corner.	127
Figure 4.39	Pathways of carbon diffusion through the polycrystalline Ni foil at (a) 950 °C and (b) 1030 °C through the grain boundary of Ni (black arrows) and through the Ni grain (red arrows).	129
Figure 4.40	Optical micrograph of the web-like graphitic carbon grown at the inner surface of Ni at 1030 °C for 3 min.	129
Figure 4.41	Separation of bilayer graphene from Ni foil by nitric acid. (a)	133

Beginning of the process. (b) Completely separated bilayer graphene, Ni foil is submerged into nitric acid and *the white box helps to locate the separated graphene floating at the solution surface.*

- Figure 4.42 Photograph of the Ni foil covered with monolayer graphene in a solution of iron nitrate of a concentration of 0.2 mol/L after 2 days. 135
- Figure 4.43 *(a) Progress for bilayer graphene separation from Ni foil in iron nitrate solution (0.50 mol/L) from left to right; the white box indicating the separated graphene. (b) Photograph of the six bilayer graphenes after transfer on silicon wafer (with 1000 Å silicon oxide) obtained from their respective cycle, white boxes indicating the locations of graphene. (c) HRTEM image of the bilayer graphene separated under the sixth cycle.* 136
- Figure 4.44 (a) Raman spectra for six bilayer graphene samples after separation from Ni foil and transfer onto a *silicon/silicon oxide wafer*. Raman maps of (b) $\text{fwhm}_{2\text{D}}$ and (c) $\text{I}_{2\text{D}}/\text{I}_{\text{G}}$ of the bilayer graphene grown under the sixth cycle. 137
- Figure 4.45 XRD patterns of the nickel foil after CVD growth of (black) monolayer graphene, (blue) bilayer graphene and (red) multilayer graphene. 139
- Figure 4.46 AFM images for (a) the nickel foil before the CVD reaction, (b) the nickel foil after CVD reaction and separation with iron nitrate, (c) nickel foil after the CVD reaction and separation with nitric acid and (d) the nickel foil obtained after the separation process by the iron nitrate solution and polished with sand paper (800 mesh). The dimensions for all the images are 15 μm x 15 μm . 141

Figure 4.47	Optical images of graphene transferred from Ni foil for (a) graphene grown on a fresh new Ni foil, (b) graphene grown on unpolished Ni foil after separation with iron nitrate for the preceding graphene growth (c) graphene grown on unpolished Ni foil after separation with nitric acid for the preceding graphene growth. Areas with gold color are contaminations by nickel.	142
Figure 4.48	XRD patterns of the nickel foil after the CVD reaction (red), after the CVD reaction and graphene separation using iron nitrate (blue) and nitric acid (black).	143
Figure 4.49	Schematic illustrating interactions and etching mechanism during the separation of graphene with (a) a smooth surface and (b) a corrugated surface. The particles indicating the Ni grains, black line represents the graphene layer and the arrows show interacting paths. (c) HRTEM image for encapsulated Ni particles in graphene that grown from Ni with rough surface.	144
Figure 4.50	Schematic diagram of graphene and Ni ₃ C formation. (a) At elevated temperature, methane decomposes at the surface and carbon atoms dissolve into Ni foil. (b) Graphene formation by segregation of carbon from Ni above a threshold during the cooling process. (c) Very rapid cooling: inhibition of carbon diffusion to the surface of Ni. Red circles indicating hydrogen, meanwhile black circle represent carbon atoms.	148

LIST OF ABBREVIATIONS

μm	Micron
AFM	Atomic force microscopy
Ar	Argon
at%	Atomic percentage
atm	Atmospheric pressure
Au	Gold
C	Carbon
CH ₄	Methane
C ₂ H ₆	Ethane
C ₃ H ₈	Propane
C ₄ H ₁₀	Butane
Co	Cobalt
Cu	Copper
cm	Centimeter
CVD	Chemical vapor deposition
C ₆₀	Buckminsterfullerene
CO ₂	Carbon dioxide
CNT	Carbon nanotube
D	Diameter
DFT	Density functional theory
EDS	Energy dispersive spectrometer
EVA	Poly(ethylene co-vinyl acetate)
Fe	Iron
fwhm _{2D}	Full width half maximum of 2D-band
GC	Gas Chromatography
GO	Graphene oxide
H ₂	Hydrogen gas
H ₂ S	Hydrogen Sulfide
He	Helium
HNO ₃	Acid nitrate
HOPG	Highly ordered pyrolytic graphite

HRTEM	High resolution transmission electron microscope
ICT	Information and communication technology
I_{2D}/I_G	Intensity ratio of 2D-band over G-band
IPA	Isopropyl alcohol
Ir	Iridium
J	Joule
K	Kelvin
keV	Kilo electron Volt
KOH	Potassium hydroxide
kV	KiloVolt
L	Length
m	meter
MD	Molecular dynamics
min	Minute
MIT	Massachusetts Institute of Technology
MET	Mechano-electro-thermal
ML	Monolayer
mm	Milimeter
Mg	Magnesium
MOHE	Ministry of Higher Education
mol/L	Mol per liter
MOSTI	Ministry on Science, Technology & Innovation
MR	Member ring
mW	MegaWatt
N_2	Nitrogen
NaOH	Sodium hydroxide
Ne	Neon
Ni	Nickel
Ni_3C	Nickel carbide
Ni TFB	Transene Thin Film Nickel Etchants

nm	Nanometer
O	Oxygen
O ₂	Oxygen gas
OD	Outer diameter
Pa	Pascal
PBU	Polybutadiene
PC	Poly(bisphenol-A-carbonate)
PDMS	Polydimethylsiloxane
PECVD	Plasma enhanced chemical vapor deposition
PET	Polyethylene terephthalate
PI	Polyimide
PMMA	Poly(methyl methacrylate),
Pt	Platinum
R2R	Roll-to-roll
R&D	Research and Development
Ru	Ruthenium
s	Second
scm	Standard cubic centimeter
SiC	Silicon carbide
SiO ₂	Silicon oxide
SSPO1	2-(diphenylphosphoryl) spirofluorene
SW	Stone–Wales
TCD	Thermal conductivity detector
TEM	Transmission electron microscopy
Tpa	Terapascal
TRT	Thermal release tape
UHV	Ultra high vacuum
USA	United State of America
V	Volt
Xe	Xenon
XRD	X-ray Diffraction

LIST OF SYMBOLS

%	Percent
π	pi
$^{\circ}\text{C}$	Degree Celcius
\AA	Angstrom

**PENUMBUHAN GRAFENA BERLAPIS TUNGGAL PADA NIKEL
POLIHABLURAN DAN PEMANGKIN DWILOGAM NIKEL-KUPRUM DAN
KAJIAN UNTUK PENGGUNAAN SEMULA PEMANGKIN NIKEL**

ABSTRAK

Grafena merupakan struktur karbon dengan ketebalan satu atom. Grafena terdedah semua atomnya ke medium sekitar. Selepas penemuan grafena pada 2004, ia menjadi subjek utama penyelidikan di seluruh dunia. Grafena mempunyai sifat-sifat yang luar biasa dari segi mekanikal, optik, haba dan elektrik. Sifat-sifat tersebut menjadikan grafena berpotensi digunakan dalam pelbagai aplikasi. Pemendapan wap kimia bermangkin (CVD) adalah saluran yang paling baik untuk menghasilkan grafena berskala wafer, kerana teknik ini mempunyai kelebihan dalam proses pemisahan grafena daripada pemangkin selepas CVD. Dengan bantuan penyejukan pantas, grafena berlapis tunggal berjaya dibentuk pada foil nikel polihabluran dibawah CVD tekanan atmosfera, dengan suhu 850 °C, tekanan separa metana 0.2 atm and 5 min tempoh reaksi. Tetapi grafena berlapis tunggal gagal dibentuk dengan menggunakan foil kuprum sahaja. Penyejukan pantas selepas CVD mendorong pelindapkejutan aktiviti pemangkin dan menghadkan kadar difusi karbon dalam nikel ke permukaan nikel. Proses ini memudahkan pembentukan grafena berlapis tunggal berskala wafer. Untuk meningkatkan keseragaman grafena berlapis tunggal, satu teknik mudah digunakan untuk menumbuh grafena berlapis tunggal secara serentak pada kedua-dua foil nikel polihabluran dan foil kuprum polihabluran, pada suhu 950 °C, tekanan separa metana 0.2 atm and 5 min tempoh reaksi. Struktur grafena yang seragam dan berkualiti tinggi dapat dibukti dengan spektroskopi Raman dan mikroskop transmisi electron resolusi tinggi. Sistem pemangkin dwilogam yang dicadang membolehkan pengawalan difusi karbon ke permukaan dalam foil Ni dan

Cu. Khususnya, kebolehcapaian karbon dapat dikurangkan pada permukaan Ni dalaman, manakala Cu memainkan peranan sebagai penghalang karbon. Mekanisme pertumbuhan grafena berlapis tunggal dapat dibantu dengan difusi karbon melalui bijian Ni dan sempadan bijian Ni. Daya penggerak untuk difusi karbon datang daripada kepekatan kecerunan karbon antara permukaan yang kaya dengan karbon dan permukaan kurang karbon. Sempadan bijian Ni telah terbukti memainkan peranan yang penting dalam kawalan difusi karbon semasa peringkat pertumbuhan. Dengan bantuan penyejukan pantas, proses pelindapkejut mengurangkan jumlah atom karbon diasing dari Ni, hanya atom karbon yang terletak berhampiran permukaan Ni mempunyai masa yang cukup untuk mengasing dan membentuk grafena. Sementara itu difusi atom karbon dalam tengah foil Ni telah dihalang dan lepas itu membentuk Ni_3C . Ni_3C dikenali sebagai perlindungan yang baik terhadap kakisan. Kehadiran Ni_3C digabungkan dengan penggunaan ferum nitrat (0.5mol/L) sebagai bahan punar lemah semasa pemisahan grafena, foil Ni boleh digunakan semula sehingga 6 kali tanpa menyebabkan sisihan yang besar terhadap kualiti dan keseragaman grafena berlapis dua. Ni_3C ternyata mampu untuk menghadkan kesan punaran foil Ni. Kerja-kerja ini telah berjaya mempamerkan cara yang mudah dan novel untuk mensintesis grafena berlapis tunggal dengan kualiti yang tinggi

**SYNTHESIS OF MONOLAYER GRAPHENE ON POLYCRYSTALLINE
NICKEL AND NICKEL-COPPER BIMETALLIC CATALYST AND STUDY
TOWARD THE REUSE OF NICKEL CATALYST**

ABSTRACT

Graphene is a layer of sp^2 hybridized carbon atoms with a thickness of only one atom, which exposed most of its atoms to the surrounding medium. Since the discovery of graphene in 2004, it has become the main subject of research around the world. The attractiveness of graphene is mainly attributed to its remarkable mechanical, optical, thermal and electrical properties, enabling graphene to be potentially used in various applications. To date, CVD is the promising method to produce wafer-scale graphene, because it allows an easier separation of graphene from the catalytic substrate. With the assist of fast cooling, monolayer graphene was grown directly on polycrystalline Ni foil under atmospheric pressure CVD with temperature of 850 °C, methane partial pressure of 0.2 atm and reaction duration of 5 min. However, monolayer graphene could not be formed on Cu under the chosen CVD conditions. Fast cooling after CVD allowed the quenching of the activity of the catalyst and limiting diffusion of dissolved carbon to the surface of Ni, which later facilitate the formation of predominantly wafer scale monolayer graphene. To further improve the uniformity of monolayer graphene, a facile technique was applied to grow monolayer graphene simultaneously on both polycrystalline Ni and Cu foils using a Ni-Cu bilayer catalyst at temperature of 950 °C, methane partial pressure of 0.2 atm and reaction duration of 5 min. High uniformity and quality of the crystalline structure of the grown graphene was evidenced by Raman spectroscopy mapping and High Resolution Transmission Electron Microscope. The straightforward bimetallic catalytic system allows the control of carbon diffusion to the interface of Ni and Cu.